

ABSTRACT OF THE DISCLOSURE

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A semiconductor laser has an active region which includes at least a quantum well layer and upper and lower optical waveguide layers and is of $\text{In}_x\text{Ga}_{1-x}\text{As}_y\text{P}_{1-y}$ ($0 \leq x \leq 1$, $0 \leq y \leq 1$). Upper and lower AlGaAs cladding layers are formed on opposite sides of the active region. At least one of the optical waveguide layers is not smaller than $0.25\mu\text{m}$ in thickness, and a part of the upper cladding layer on the upper optical waveguide layer is selectively removed up to the interface of the upper cladding layer and the upper optical waveguide layer.